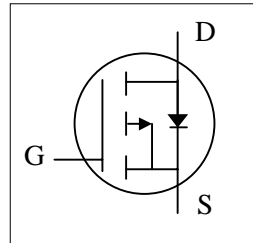
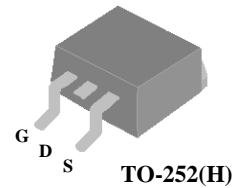


- ▼ Lower Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



| | |
|--------------|--------------|
| BV_{DSS} | -40V |
| $R_{DS(ON)}$ | 52m Ω |
| I_D | -17A |



Description

XSEMI MOSFETs provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|-----------------------------|--------------------------------------|------------|---------------------|
| V_{DS} | Drain-Source Voltage | -40 | V |
| V_{GS} | Gate-Source Voltage | +20 | V |
| $I_D@T_C=25^\circ\text{C}$ | Drain Current, V_{GS} @ 10V | -17 | A |
| $I_D@T_C=100^\circ\text{C}$ | Drain Current, V_{GS} @ 10V | -11 | A |
| I_{DM} | Pulsed Drain Current ¹ | -60 | A |
| $P_D@T_C=25^\circ\text{C}$ | Total Power Dissipation | 25 | W |
| | Linear Derating Factor | 0.2 | W/ $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |

Thermal Data

| Symbol | Parameter | Value | Units |
|--------|---|-------|---------------------------|
| Rthj-c | Maximum Thermal Resistance, Junction-case | 5.0 | $^\circ\text{C}/\text{W}$ |
| Rthj-a | Maximum Thermal Resistance, Junction-ambient (PCB mount) ³ | 62.5 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics @T_j=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------------|--|---|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =-250uA | -40 | - | - | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =-10V, I _D =-8A | - | - | 52 | mΩ |
| | | V _{GS} =-4.5V, I _D =-6A | - | - | 90 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =-250uA | -1 | - | -3 | V |
| g _{fs} | Forward Transconductance | V _{DS} =-10V, I _D =-8A | - | 9.6 | - | S |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =-40V, V _{GS} =0V | - | - | -10 | uA |
| | Drain-Source Leakage Current (T _j =125°C) | V _{DS} =-32V, V _{GS} =0V | - | - | -250 | uA |
| I _{GSS} | Gate-Source Leakage | V _{GS} = +20V, V _{DS} =0V | - | - | +100 | nA |
| Q _g | Total Gate Charge ² | I _D =-8A | - | 7.8 | 12.5 | nC |
| Q _{gs} | Gate-Source Charge | V _{DS} =-32V | - | 1.7 | - | nC |
| Q _{gd} | Gate-Drain ("Miller") Charge | V _{GS} =-4.5V | - | 4.8 | - | nC |
| t _{d(on)} | Turn-on Delay Time ² | V _{DS} =-20V | - | 8 | - | ns |
| t _r | Rise Time | I _D =-8A | - | 17 | - | ns |
| t _{d(off)} | Turn-off Delay Time | R _G =3.3 Ω | - | 22 | - | ns |
| t _f | Fall Time | V _{GS} =-10V | - | 23 | - | ns |
| C _{iss} | Input Capacitance | V _{GS} =0V | - | 530 | 850 | pF |
| C _{oss} | Output Capacitance | V _{DS} =-25V | - | 110 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | f=1.0MHz | - | 75 | - | pF |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|------------------------------------|---|------|------|------|-------|
| V _{SD} | Forward On Voltage ² | I _S =-8A, V _{GS} =0V | - | - | -1.2 | V |
| t _{rr} | Reverse Recovery Time ² | I _S =-8A, V _{GS} =0V, | - | 21 | - | ns |
| Q _{rr} | Reverse Recovery Charge | dI/dt=-100A/μs | - | 14 | - | nC |

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

XSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

XSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

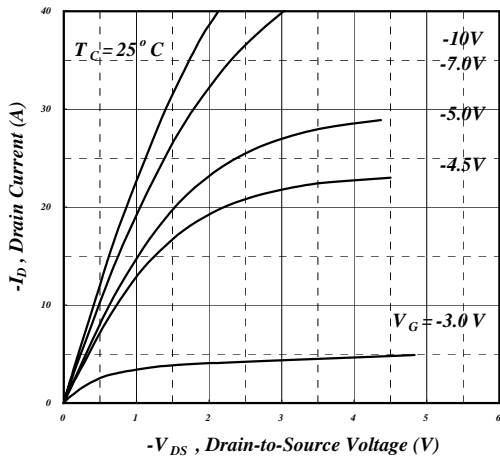


Fig 1. Typical Output Characteristics

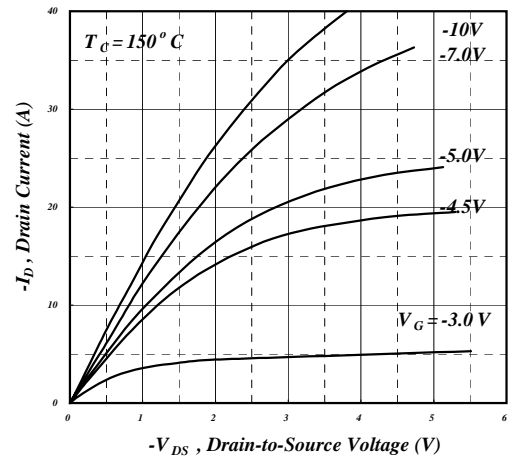


Fig 2. Typical Output Characteristics

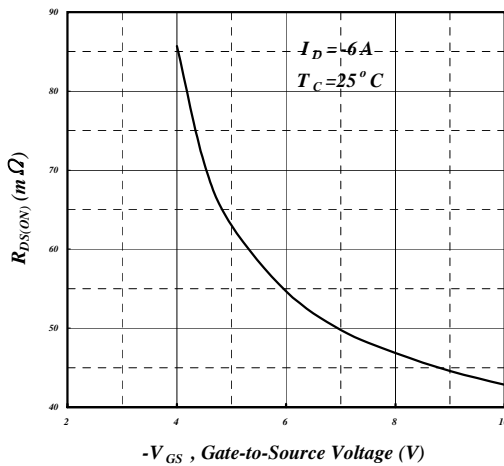


Fig 3. On-Resistance v.s. Gate Voltage

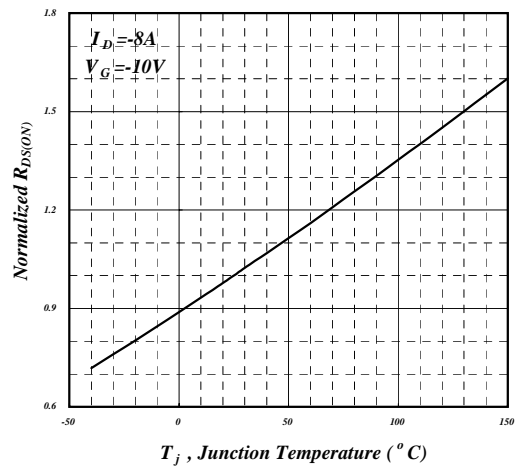


Fig 4. Normalized On-Resistance v.s. Junction Temperature

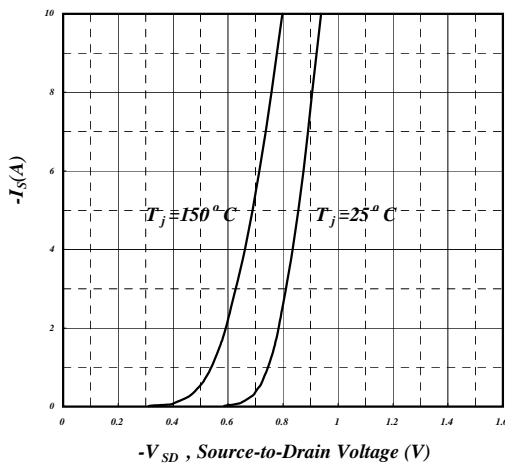


Fig 5. Forward Characteristic of Reverse Diode

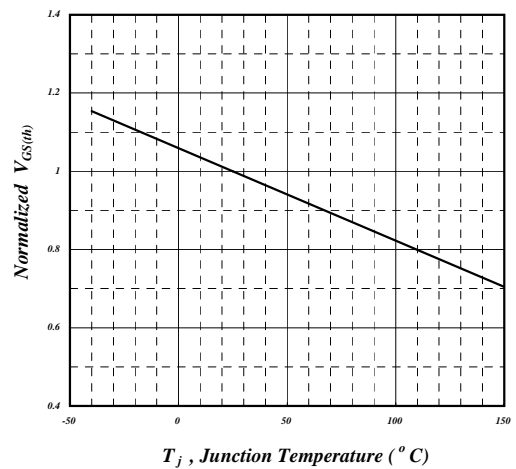


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

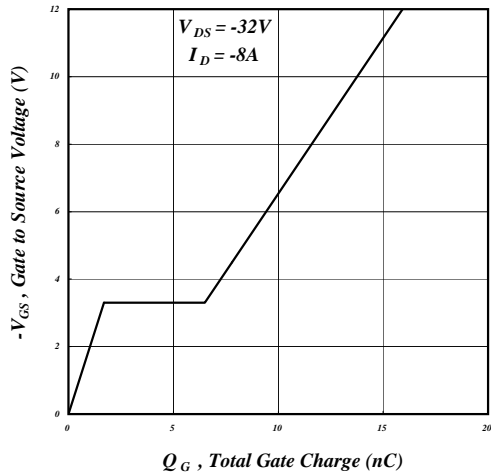


Fig 7. Gate Charge Characteristics

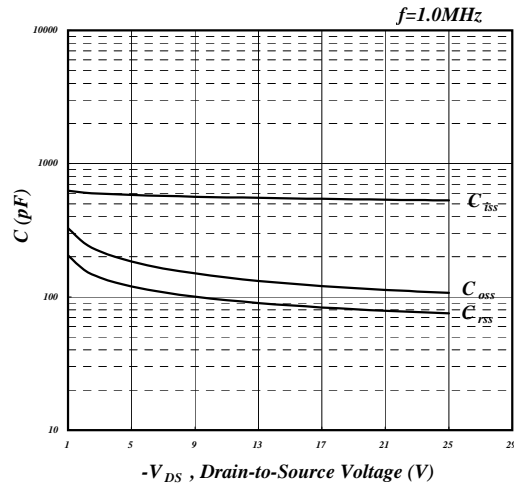


Fig 8. Typical Capacitance Characteristics

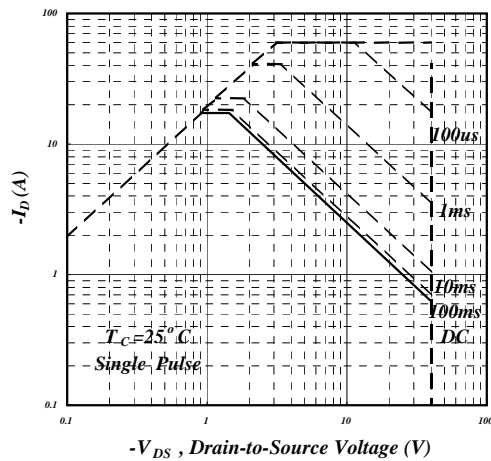


Fig 9. Maximum Safe Operating Area

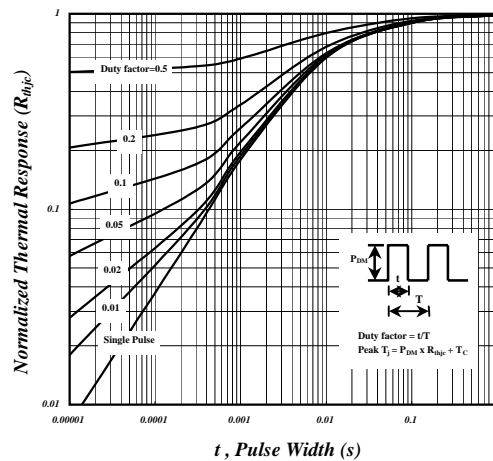


Fig 10. Effective Transient Thermal Impedance

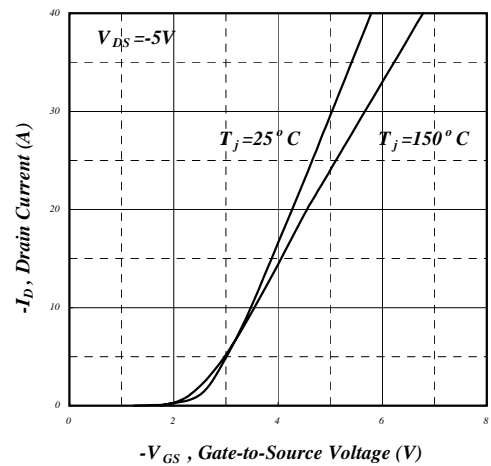


Fig 11. Transfer Characteristics

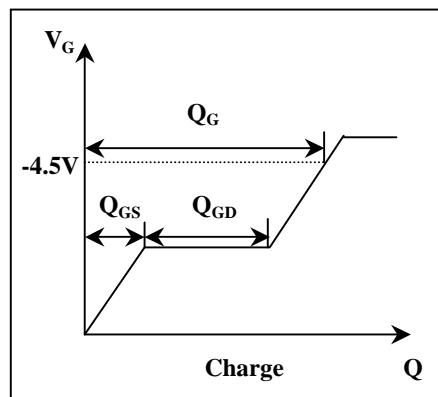
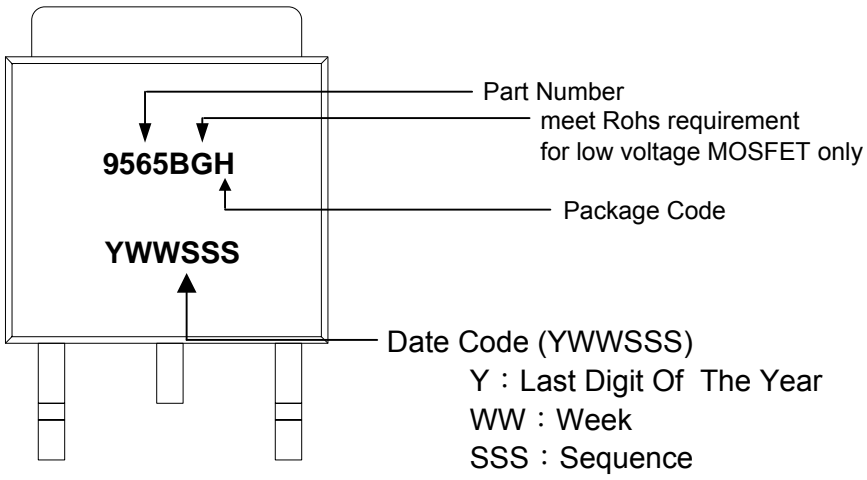
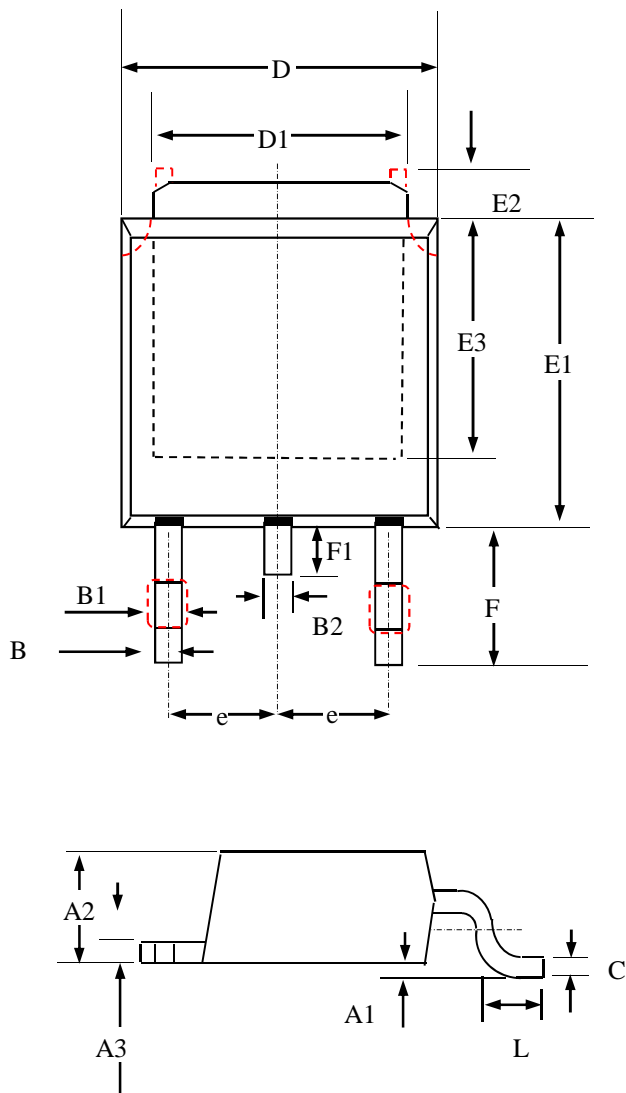


Fig 12. Gate Charge Waveform

MARKING INFORMATION



Package Outline : TO-252



| SYMBOLS | Millimeters | | |
|---------|-------------|-------|------|
| | MIN | NOM | MAX |
| A2 | 2.18 | 2.30 | 2.40 |
| A3 | 0.40 | 0.50 | 0.65 |
| B | 0.40 | 0.70 | 1.00 |
| B1 | 0.50 | 0.85 | 1.20 |
| D | 6.00 | 6.50 | 6.80 |
| D1 | 4.80 | 5.35 | 5.90 |
| E3 | 4.00 (ref.) | | |
| F | 2.00 | 2.63 | 3.05 |
| F1 | 0.50 | 0.85 | 1.20 |
| E1 | 5.00 | 5.70 | 6.30 |
| E2 | 0.50 | 1.10 | 1.80 |
| e | 2.3 (ref) | | |
| C | 0.35 | 0.525 | 0.70 |
| A1 | 0.00 | — | 0.25 |
| B2 | — | — | 1.25 |
| L | 0.90 | 1.34 | 1.78 |

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.
3. Thermal PAD, Body and Pin contour is for reference, it may has little difference by option.

TO-252 FOOTPRINT :

